

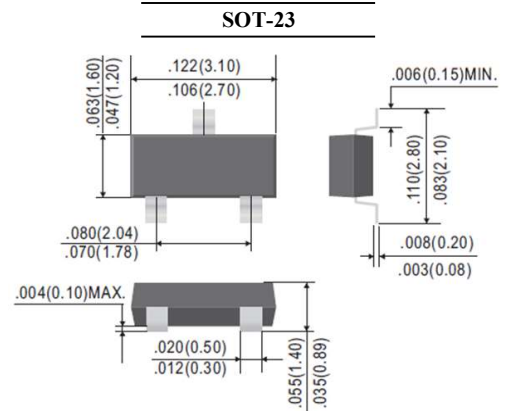
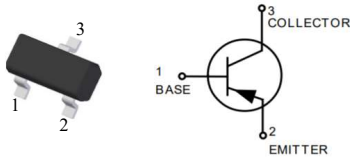


MMBT2907AH

PNP TRANSISTOR

FEATURES

- The transistor is subdivided into one group according to its DC current gain.
- Suffix "H" indicates Halogen-free parts, ex. MMBT2907AH



Dimensions in inch and (millimeter)

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CB0}	-60	V
Collector Emitter Voltage	V_{CEO}	-60	V
Emitter Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Max.	Unit
DC Current Gain	$I_C = -0.1\text{mA}$, $V_{CE} = -10\text{V}$	h_{FE}	75	-	-
	$I_C = -1\text{mA}$, $V_{CE} = -10\text{V}$		100	-	
	$I_C = -10\text{mA}$, $V_{CE} = -10\text{V}$		100	-	
	$I_C = -150\text{mA}$, $V_{CE} = -10\text{V}$		100	300	
	$I_C = -500\text{mA}$, $V_{CE} = -10\text{V}$		50	-	
Collector Base Cutoff Current	$V_{CB} = -50\text{V}$	I_{CBO}	-	-10	nA
Collector Base Breakdown Voltage	$I_C = -10\mu\text{A}$	$V_{(BR)CBO}$	-60	-	V
Collector Emitter Breakdown Voltage	$I_C = -10\text{mA}$	$V_{(BR)CEO}$	-60	-	V
Emitter Base Breakdown Voltage	$I_E = -10\mu\text{A}$	$V_{(BR)EBO}$	-5	-	V
Collector Saturation Voltage	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$	$V_{CE(sat)}$	-	-0.4	V
	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$		-	-1.6	
Base Saturation Voltage	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$	$V_{BE(sat)}$	-	-1.3	V
	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$		-	-2.6	



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Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Max.	Unit
Gain Bandwidth Product	$I_C = -50\text{mA}$, $V_{CE} = -20\text{V}$, $f = 100\text{MHz}$	f_T	200	-	MHz
Collector Output Capacitance	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$	C_{ob}	-	8.0	pF
Turn-on Time	$V_{CC} = -30\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$	t_{on}	-	45	ns
Delay Time	$V_{CC} = -30\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$	t_d	-	10	ns
Rise Time	$V_{CC} = -30\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$	t_r	-	40	ns
Turn-off Time	$V_{CC} = -6\text{V}$, $I_C = -150\text{mA}$, $-I_{B1} = -I_{B2} = 15\text{mA}$	t_{off}	-	100	ns
Storage Time	$V_{CC} = -6\text{V}$, $I_C = -150\text{mA}$, $-I_{B1} = -I_{B2} = 15\text{mA}$	t_s	-	80	ns
Fall Time	$V_{CC} = -6\text{V}$, $I_C = -150\text{mA}$, $-I_{B1} = -I_{B2} = 15\text{mA}$	t_f	-	30	ns



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RATINGS AND CHARACTERISTIC CURVES

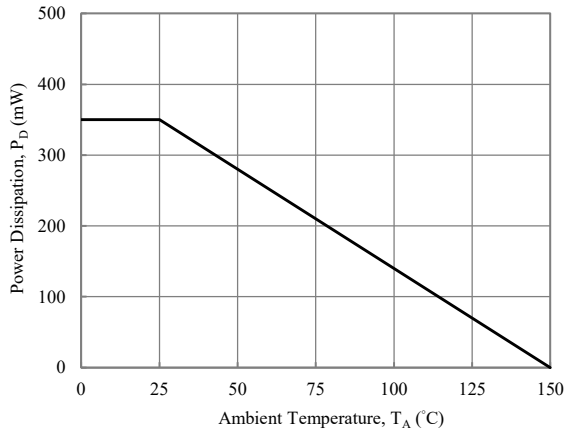


Fig. 1-Power Derating Curves

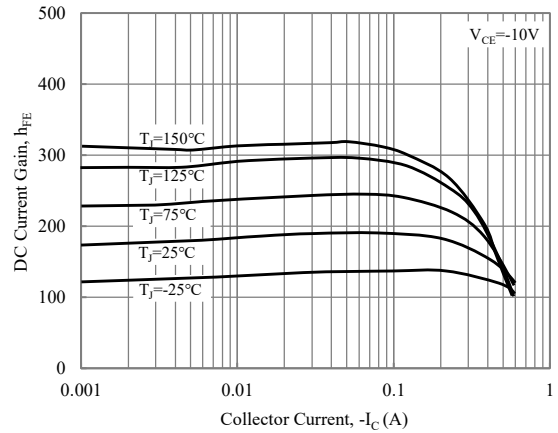


Fig. 2-Current Gain vs Collector Current

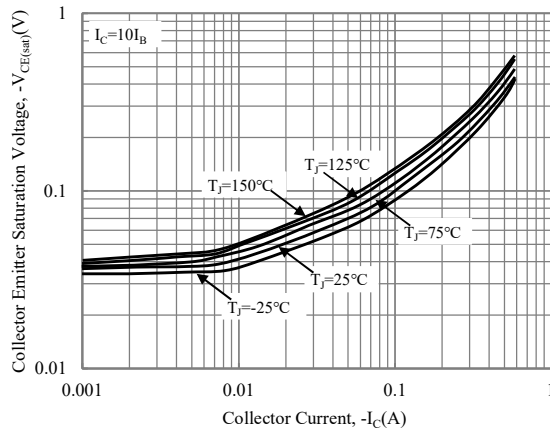


Fig. 3-Collector Emitter Saturation Voltage vs Collector Current

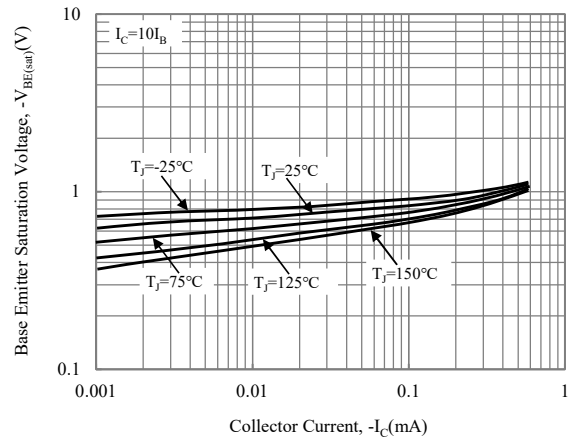


Fig. 4-Base Emitter Saturation Voltage vs Collector Current

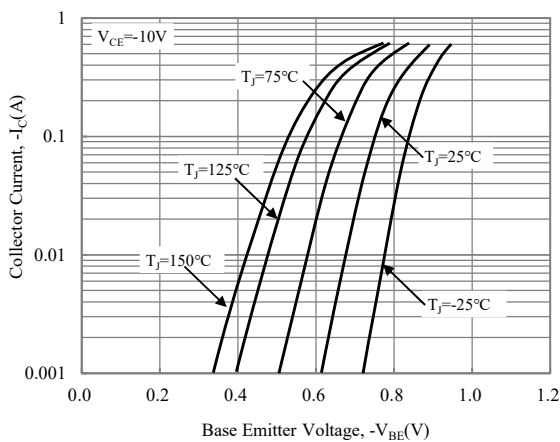


Fig. 5-Base Emitter Voltage vs Collector Current

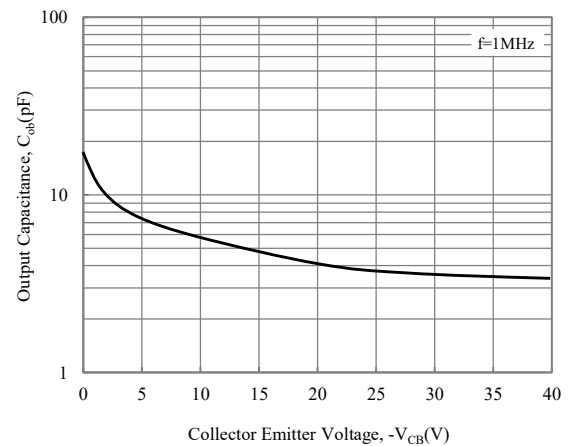


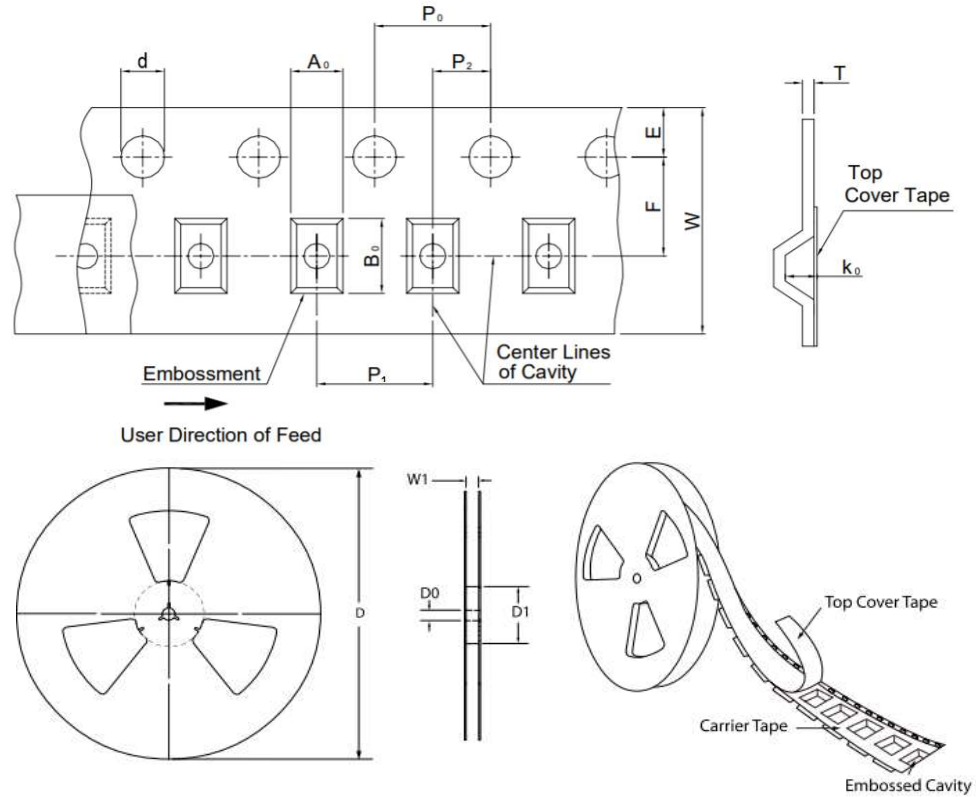
Fig. 6-Capacitance



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TAPE & REEL SPECIFICATION



Item	Symbol	SOT-23
Carrier width	A_0	3.20 ± 0.10
Carrier length	B_0	2.80 ± 0.10
Carrier depth	K_0	1.55 ± 0.10
Sprocket hole	d	1.50 ± 0.10
Reel outside diameter	D	178.00 ± 2.00
Feed hole width	D_0	13.00 ± 0.50
Reel inner diameter	D_1	MIN. 50.00
Sprocket hole position	E	1.75 ± 0.10
Punch hole position	F	3.50 ± 0.10
Sprocket hole pitch	P_0	4.00 ± 0.10
Punch hole pitch	P_1	4.00 ± 0.10
Embossment center	P_2	2.00 ± 0.10
Overall tape thickness	T	MAX. 0.60
Tape width	W	8.00 ± 0.30
Reel width	W_1	MAX. 10.00

ORDER INFORMATION

Package	Reel Size	Quantity
SOT-23	7"	3,000

MARKING CODE

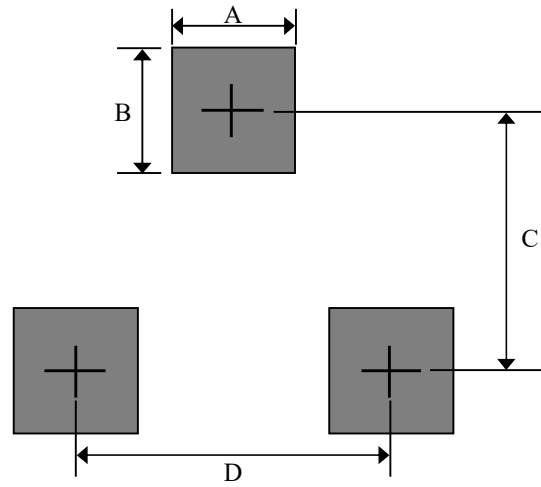
Part Number	Marking Code
MMBT2907AH	2F



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PNP TRANSISTOR

SUGGESTED SOLDER PAD LAYOUT



Unit : mm

PACKAGE	A	B	C	D
SOT-23	0.80	1.00	2.40	1.90